herrih Hirt. 12/10/04 / (23 pp.)

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
	981	(372/36).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 17:08
L2	81	1 and lens and resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 17:08
S1	4	"667775" ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 13:36
S2	2	"5177753".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/09/13 13:36
S3	2	("4829531").PN.	US PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 17:07
S4	2	("4829531").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 16:31
\$5	2	("5488678"). PN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 16:35
S6	2	("5825952").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 09:54
S7	0	jp-04449242\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 16:36

S8	1	jp-04249442\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 16:39
\$9 \$10	7	jp-02511591\$-\$.did. "511591"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR OR	ON ON	2002/10/31 16:38
S11	5296	(372/43).ccLS.	IBM_TDB US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 17:12
S12	876	(372/44).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 17:12
SI3	3317	(372/45).CCLS	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	-2002/10/31 17:12
S14	2608	(372/46).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 17:12
S15	122	(372/47).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 17:12
S16	415	(372/48).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 17:12

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S17	601	(372/49).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 17:12
S18	1634	(372/50) CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/10/31 17:12
S19	12010	((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 17:13
S20	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and mold\$2 near4 resin and diffusion adj plate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	ON.	2002/10/31 17:14
S21	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and mold\$2 near12 resin near12 diffusion near12 plate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 17:15
S22	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and mold\$2 near12 resin near12 diffusion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	ÖR	ON	2002/10/31 17:16
S23	8	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and mold\$2 near12 resin- and light near12 diffus\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 17:17
S24	58	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and mold\$2 near12 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 18:35

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S25	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and spot adj size near12 resin near12 refractive adj index	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 18:36
S26	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and spot adj size near12 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/10/31 18:36
S27	1	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near12 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:14
\$28	305	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:16
S29	305	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:23
S30	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near4 ".mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:24
S31	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near12 ".mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:24

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S32	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near12 \$1".mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:25
S33	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near12 "8.mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:26
S34	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near12 "9.mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:26
S35	0	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near12 "10.mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:27
S36	43	(((372/43).CCLS.) or ((372/44). CCLS.) or ((372/45).CCLS.) or ((372/46).CCLS.) or ((372/47). CCLS.) or ((372/48).CCLS.) or ((372/49).CCLS.) or ((372/50). CCLS.)) and (beam adj size or beam adj diameter or spot adj size) near12 (larger or greater)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 11:29
S37	4	"6111283"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 13:42
S38	2	("5502320").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 13:42

	T	T	 	1		
S39		("5986304").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 13:43
S40	2	("6111283").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/01 13:43
S41	173	laser.ti. and 372/43.ccls. and (mqw or multiple adj quantum adj well)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 14:29
S42	33.	laser.ti. and 372/43.ccls. and (mqw or multiple adj quantum adj well) and high adj power	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ÖN	2002/11/01-14:29
S43	0	laser.ti. and 372/43.ccls. and (mqw or multiple adj quantum adj well) and high adj power near12 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 14:30
S44	3	laser.ti. and 372/43.ccls. and (mgw or multiple adj quantum adj well) and high adj power and spot adj size	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 15:22
S45	6	laser.ti. and 372/43.ccls. and ((second or additional or plurality) adj laser adj (chip or die))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:26
S46	0	laser.ti. and 372/43.ccls. and molded adj resin near15 epoxy near15 silica	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:28
S47	1	laser.ti. and 372/43.ccls. and epoxy near15 silica near15 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:28
S48	10 10 10 1 1 1 1 1 1 1 1 1 1 1 1 1 1 1	laser.ti. and 372/43.ccls. and epoxy same silica same resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:29

S49	0	laser.ti. and 372/43.ccls. and resin near15 mixture near15 (silica or epoxy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:30
S50		372/43.ccls. and resin near15 mixture near15 (silica or epoxy)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:32
S51	2742	resin near6 silica near6 epoxy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:34
S52	6327	molded adj resin near (resin near6 silica near6 epoxy) epoxy near15 silica	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ΘN	2002/11/01 16:34
S53	109	molded adj resin near (resin near6 silica near6 epoxy) epoxy near15 silica and laser.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 16:34
S54	7	molded adj resin near (resin near6 silica near6 epoxy) (mixture or mixed) near15 epoxy near15 silica and laser.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 17:38
S55	7	(seal or molded) adj resin near (resin near6 silica near6 epoxy) (mixture or mixed) near15 epoxy near15 silica and laser.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 17:39
S56	29	(seal or molded) near3 resin near (resin near6 silica near6 epoxy) (mixture or mixed) near15 epoxy near15 silica and laser.ti,ab.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 18:08
S57	20	jp-0818163\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 18:09
S58	.0	jp-0818163\$-\$.did. and double adj sealing	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 18:09

S59	116	double adj sealing and resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 18:09
S60	23	double adj sealing near12 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 18:24
S61	1977	(mixing or mix or mixture) near12 resin and (light adj emitting or light-emitting or laser).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 18:26
S62	14	(mixing or mix or mixture) near12 resin near12 refractive adj index and (light adj emitting or light-emitting or laser).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 19:06
S63	19	(thermal adj resistance or heat adj capacity) near15 (chip or die) and laser.ti,ab,clm. and ("372"/\$6.ccls. or "257"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 19:22
S64	0	(thermal adj resistance or heat adj capacity) near15 (chip or die) and heat adj sink near15 (contain or container) and laser.ti,ab,clm. and ("372"/\$6.ccls. or "257"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	O X	2002/11/01 19:24
S65	0	(thermal adj resistance or heat adj capacity) near15 (chip or die) and heat adj sink near15 (contain or container) and laser.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/01 19:24
S66	26	(thermal adj resistance or heat adj capacity) near15 (chip or die) and heat adj sink near15 (contain or container)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ΘN	2002/11/01-19:25
S67	170	(372/4\$1.ccls. or 372/50.ccls.) and thermal adj resistance	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 10:34
S68	2	(372/4\$1.ccls. or 372/50.ccls.) and (thermal adj resistance near15 "deg/W")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON Section 1	2002/11/02 10:37

S69	2	(372/4\$1.ccls. or 372/50.ccls.) and	US-PGPUB;	OR	ON	2002/11/02 10:37
		"deg/W"	USPAT; EPO; JPO; DERWENT; IBM_TDB			,
S70	2	(372/4\$1.ccls. or 372/50.ccls. or	US-PGPUB;	OR	ON	2002/11/02 10:40
		257/79.ccls. or 257/8\$1.ccls. or 257/9\$1.ccls. or 257/100.ccls. or	USPAT; EPO; JPO;			
1		257/101.ccls. or 257/102.ccls. or	DERWENT;			
		257/103.ccls.) and "deg/W"	IBM_TDB			
S71	3654	(372/4\$1.ccls. or 372/50.ccls. or 257/79.ccls. or 257/8\$1.ccls. or 257/9\$1.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and ("deg/W" or (thermal resistance near12 heat sink))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 10:41
S72	2868	(372/4\$1.ccls. or 372/50.ccls. or	US-PGPUB;	OR	ON	2002/11/02 10:42
		257/79.ccls. or 257/8\$1.ccls. or 257/9\$1.ccls. or 257/100.ccls. or	USPAT; EPO; JPO;			
l de t		257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and ("deg/W" or	DERWENT; IBM TDB			
		(thermal resistance near12 heat adj				
		sink))				
S73	2867	(372/4\$1.ccls. or 372/50.ccls. or 257/79.ccls. or 257/8\$1.ccls. or 257/9\$1.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and ("deg/W" or (thermal resistance near6 heat adj sink))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 10:43
S74	365	(372/4\$1.ccls. or 372/50 ccls. or 257/79.ccls. or 257/8\$1.ccls. or	US-PGPUB; USPAT;	OR	ON	2002/11/02 10:43
		257/9\$1.ccls. or 257/100.ccls. or	EPO; JPO;			
		257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and ("deg/W" or	DERWENT; IBM_TDB			
\$44.5		(low near6 thermal resistance near6				
S75	2	heat adj sink)) (372/4\$1.ccls. or 372/50.ccls. or	US-PGPUB;	OR	ON	2002/11/02 10:44
,		257/79.ccls. or 257/8\$1.ccls. or	USPAT;		ON	2002/11/02 10.44
		257/9\$1.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or	EPO; JPO; DERWENT;			
		257/103.ccls.) and ("deg/W" or (low near6 thermal near6 resistance	IBM_TDB			
		near6 heat adj sink))				
S76	1	(372/4\$1.ccls. or 372/50.ccls. or	US-PGPUB;	OR	ON	2002/11/02 10:46
	27 7	257/79.ccls. or 257/8\$1.ccls. or 257/9\$1.ccls. or 257/100.ccls. or	USPAT; EPO; JPO;			
		257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and ((low or lower)	DERWENT; IBM_TDB		8	
-1 - Fa - 1.		near6 thermal near6 resistance				
	4.8 11.5	near6 heat adj sink)	ing and the second seco			

S77	19	(372/4\$1.ccls. or 372/50.ccls. or 257/79.ccls. or 257/8\$1.ccls. or 257/9\$1.ccls. or 257/100.ccls. or 257/101.ccls. or 257/102.ccls. or 257/103.ccls.) and (thermal adj resistance near6 heat adj sink)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 10:49
S78	1	thermal adj resistance near3 copper near12 "deg/W"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:17
S79	9	(thickness or thick) near4 heat adj sink and ("257"/\$6.ccls. or "372"/\$6.ccls.) and (area near4 bonded)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 11:19
\$80 \$81	25	(US-5307362-\$ or US-5373519-\$ or US-5422905-\$ or US-6448583-\$ or US-6049423-\$ or US-5105237-\$ or US-5970081-\$ or US-5734672-\$ or US-6219364-\$ or US-6049125-\$ or US-6758951-\$ or US-6133631-\$ or US-6144684-\$ or US-4829531-\$ or US-5488678-\$ or US-5825952-\$ or US-5907571-\$ or US-5355385-\$). did. or (DE-4315581-\$).did. or (JP-61176169-\$ or JP-05129730-\$). did. or (EP-257898-\$ or JP-07045811-\$ or JP-09127349-\$ or EP-483549-\$).did. heat adj sink near12 "W/deg" and (laser or light-emtting or light adj emitting).ti,ab,clm.	USPAT; EPO; JPO; DERWENT US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR OR	OFF OS	2002/11/02 11:53
S82	0.	heat adj sink near12 "W/deg" and (laser or light-emitting or light adj emitting).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:18
S83	0	heat adj sink near12 "W/deg" and ("257"/\$6.ccls. or "438"/\$6.ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:19
S84	193	heat adj sink near12 thermal adj resistance and ("257"/\$6.ccls. or "438"/\$6.ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:20

S85	43	heat adj sink near12 thermal adj resistance near12 low and ("257"/\$6.ccls. or "438"/\$6.ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:36
S86		heat adj sink near12 thermal adj resistance near12 low near12 (copper or cu) and ("257"/\$6.ccls. or "438"/\$6.ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:22
S87	43	heat adj sink near12 thermal adj resistance near12 low and ("257"/\$6.ccls. or "438"/\$6.ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:23
S88	a 0.	heat adj sink near12 thermal adj resistance near12 low near12 "K/W" and ("257"/\$6.ccls. or "438"/\$6. ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:37
S89	0	heat adj sink near12 thermal adj resistance near12 "K/W" and ("257"/\$6.ccls. or "438"/\$6.ccls. or "372"/\$6.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:38
S90	0	heat adj sink near12 (copper or cu) near12 thermal adj resistance near12 "K/W"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2002/11/02 12:39
S91	27	(US-5825952-\$ or US-6049125-\$ or US-6219364-\$ or US-6448583-\$ or US-5422905-\$ or US-5970081-\$ or US-5734672-\$ or US-6144684-\$ or US-6133631-\$ or US-6144684-\$ or US-6049423-\$ or US-4829531-\$ or US-5488678-\$ or US-4899210-\$ or US-5373519-\$ or US-5307362-\$ or US-5105237-\$ or US-5907571-\$ or US-5355385-\$ or US-5381859-\$). did. or (DE-4315581-\$).did. or (JP-61176169-\$ or JP-05129730-\$). did. or (JP-09127349-\$ or EP-257898-\$ or JP-07045811-\$ or EP-483549-\$).did.	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/11/02 13:46
S92	2	monochromatic near12 laser adj diode adj array	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/11/02 13:47
S93	5.	laser adj diode adj array near12 "same wavelength"	USPAT; EPO; JPO; DERWENT	OR	OFF	2002/11/02 17:01

S94	4	(mqw or multiple adj quantum adj well) near6 different adj wavelength	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/02 18:59
S95	2	("6049125").PN	US-PGPUB; USPAT; USOCR; EPO; JPO;	OR	OFF	2002/11/02 19:32
			DERWENT; IBM_TDB			
S96	2	("6049423").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2002/11/02 19:37
S97	14	(("6049423") or ("6049125") or ("5625402") or ("5422905") or ("5970081") or ("5355385") or ("5907571")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT;	OR	OFF	2002/11/02 19:37
			IBM_TDB			
S98	7	(("6049423") or ("6049125") or ("5625402") or ("5422905") or ("5970081") or ("5355385") or ("5907571")).PN.	USPAT; USOCR	OR	OFF	2002/11/02 19:38
S99	2	semiconductor ti, ab, clm. and laser. ti, ab, clm. and resin near12 (mixture or mix or mixing or mixed) near12 diffusion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	-2003/04/11-16:03
S10 0	6	laser.ti,ab,clm. and resin near12 (mixture or mix or mixing or mixed) near12 diffusion	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 16:07
S10	3	laser:ti,ab,clm. and (light-diffusing or light adj diffusing) near3 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11-16:08
S10 2	6	laser.ti,ab,clm. and (light-diffusing or light adj diffusing) near5 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/11 16:09

					r	
S10 3	34	(US-5614338-\$ or US-5530780-\$ or US-5976175-\$ or US-5307362-\$ or US-5355385-\$ or US-5105237-\$ or US-5373519-\$ or US-5970081-\$ or US-6133631-\$ or US-6144684-\$ or US-5734672-\$ or US-6448583-\$ or US-5422905-\$ or US-4899210-\$ or US-5625402-\$ or US-5758951-\$ or US-6219364-\$ or US-5825952-\$ or US-4829531-\$ or US-5825952-\$ or US-4829531-\$ or US-5907571-\$ or US-6049125-\$ or US-5381859-\$). did. or (US-20030031917-\$).did. or (DE-4315581-\$).did. or (JP-04037487-\$ or JP-61176169-\$ or JP-05129730-\$).did. or (GB-2142441-\$ or JP-07045811-\$ or JP-09127349-\$ or EP-257898-\$ or EP-483549-\$).did.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/04/13 17:38
S10	18	(diffuse or diffusive) near12 resin	US-PGPUB;	OR	OFF	2003/04/13 18:01
4		and laser.ti,ab,clm.	USPAT;			
			EPO; JPO; DERWENT			
C10			and the first of the control of			2002/04/12 10:02
S10 5	0	eye near12 protect\$3 and laser.ti, ab,clm. and resin near12 diffus\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/04/13 18:03
S10	0	eye near12 protect\$3 and laser.ti,	US-PGPUB;	OR	OFF	2003/04/13 18:03
6		ab,clm. and resin near12 (light-diffus\$3 or diffus\$3)	USPAT; EPO; JPO; DERWENT			
S10	156	laser.ti,ab,clm. and resin near12	US-PGPUB;	OR	OFF	2003/04/13 18:03
7	150	(light-diffus\$3 or diffus\$3)	USPAT; EPO; JPO; DERWENT	OK		
S10	4	laser.ti,ab,clm. and resin near12	US-PGPUB;	OR	OFF	2003/04/13 18:13
8		light-diffus\$3	USPAT;	er yard	idenji i	
			EPO; JPO; DERWENT			
S10	34	laser.ti,ab,clm. and resin near12	US-PGPUB;	OR	OFF	2003/04/13 18:21
9		(light near5 diffus\$3 or light-diffus\$3)	USPAT; EPO; JPO; DERWENT			2003/01/13 10:21
S11	115	semiconductor adj laser.ti,ab,clm.	US-PGPUB;	OR	OFF	2003/04/13 18:25
-0		and resin near6 lens	USPAT;			
			EPO; JPO; DERWENT	(A)		
S11	62	semiconductor adj laser.ti,ab,clm.	US-PGPUB;	OR	OFF	2003/04/13 18:25
1		and resin near3 lens	USPAT; EPO; JPO; DERWENT			

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S11 2	0	semiconductor adj laser.ti,ab,clm. and light-diffus\$3 near6 resin near3 lens	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/04/13 18:26
S11 3	1	semiconductor adj laser.ti,ab,clm. and (light near3 diffus\$3 or light-diffus\$3) near6 resin near6	US-PGPUB; USPAT; EPO; JPO;	OR	OFF	2003/04/13 18:28
		lens	DERWENT			
S11 4	1	semiconductor adj laser.ti,ab,clm. and (light near6 diffus\$3 or light-diffus\$3) near12 resin near6 lens	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/04/13 18:29
S11	1	semiconductor.ti,ab,clm. and laser. ti,ab,clm. and (light near6 diffus\$3 or light-diffus\$3) near12 resin near6 lens	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/04/13 18:34
S11 6	3	semiconductor.ti,ab,clm. and (light-emitting laser).ti,ab,clm. and (light near6 diffus\$3 or light-diffus\$3) near12 resin near6 lens	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	OFF	2003/04/13 18:34
S11	126	resin near6 lens and semiconductor	US-PGPUB;	OR	ON	2003/04/14 10:18
7		adj2 laser.ti,ab,clm.	USPAT;			
			EPO; JPO; DERWENT; IBM_TDB			
S11 8	66	resin near3 lens and semiconductor adj2 laser.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 10:21
S11 9	0	light-diffusive near6 resin near3 lens and semiconductor adj2 laser ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT;	OR	ON.	2003/04/14 10:19
			IBM_TDB			
S12 0	0	(light near6 (diffusive or diffusion or diffuse) or light-diffusive) near6 resin near3 lens and semiconductor adj2 laser.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 10:20
S12 1	0	(light near12 (diffusive or diffusion or diffuse) or light-diffusive) near12	US-PGPUB; USPAT;	OR	ON	2003/04/14 10:21
		resin near12 lens and semiconductor adj2 laser.ti;ab,clm.	EPO; JPO; DERWENT; IBM_TDB			
S12 2	34	resin near2 lens and semiconductor adj2 laser.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 10:22

S12 3	0	molded near2 resin near2 lens and semiconductor adj2 laser.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 10:22
S12 4	7	molded near12 resin near2 lens and semiconductor adj2 laser.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14:10:28
S12 5	2	laser.ti,ab,clm. and light-diffusive near6 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON .	2003/04/14 10:30
S12 6	16	laser.ti,ab,clm. and (light near3 (diffusive or diffusion or diffuse) light-diffusive) near6 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 14:40
S12 7	1	jp-07072311\$-\$.did.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 14:41
S12 8	2	("5976175").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/04/14 14:56
S12 9	0	("761240.ap.").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2003/04/14 14:56
S13 0	4 .	" 761240".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2003/04/14 14:56
S13 1	11	"5177753"	US-PGPUB; -USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/18 17:38

S13 2	2	("5177753").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/18 17:38
\$13 3	4	"667775".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 16:50
S13 4	2	("5386428").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 17:26
\$13 5	2	("5970081").PN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 18:21
S13 6	. 2	("5422905").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 18:43
S13 7	2	("4870652").PN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_ITDB	OR	OFF	2004/06/19 18:45
S13 8	0	("dualnear2lasernear2beamssamew avelength").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 18:45
S13 9	14	dual near2 laser near2 beams same wavelength	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	FOR	OFF	2004/06/19 18:57
S14 0	0	multiple adj beam adj semiconductor adj laser and "same wavelengths"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 18:58

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S14 1	19	multiple adj beam adj semiconductor adj laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR .	OFF	2004/06/19 18:58
S14 2	6	multiple adj beam adj semiconductor adj laser and wavelengths	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 19:46
S14 3	0	multiple adj beam adj semiconductor adj laser and different adj wavelengths	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 19:47
S14 4	12	multiple adj beam adj semiconductor adj laser and (wavelength wavelengths frequency frequencies)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:23
S14 5	6	(("4745294") or ("4768081") or ("5052005")).PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:23
S14 6	0	((("4745294") or ("4768081") or ("5052005")).PN.) and (wavelength frequency wavelengths frequencies)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:24
S14 7	2233	semiconductor adj laser.ti,ab,clm. and wavelength near3 range	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:25
S14 8	1117	semiconductor adj laser.ti,ab,clm. and wavelength near3 range.ti,ab, clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:26
S14 9	376	semiconductor adj laser.ti. and wavelength near3 range.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:26
S15 0		semiconductor adj laser.ti. and wavelength near3 range.clm. and resin and encapsulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:27

S15 1	0	semiconductor adj laser.ti. and wavelength near6 ".mu.m" and resin and encapsulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:28
\$15 2	0	semiconductor adj laser.ti. and wavelength near6 (micron micrometer ".mu.m") and resin and encapsulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:28
S15 3	1	semiconductor adj laser.ti. and wavelength near6 (micron micrometer ".mu.m") and resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/19 20:28
S15 4	Ô	semiconductor adj laser adj chip and resin and wavelength near6 "1. 096"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 12:55
S15 5	0	semiconductor adj laser adj chip and resin and wavelength near6 "1. 069"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 12:56
S15 6	0	semiconductor adj laser and wavelength near6 "1.069"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR.	OFF	2004/06/20 12:56
S15 7	505	semiconductor adj laser and carbon adj dioxide and wavelength	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 12:56
S15 8	0	semiconductor adj laser and carbon adj dioxide and wavelength near6 ". mu.m"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 12:56
S15 9	13	semiconductor adj laser and carbon adj dioxide and wavelength near6 micron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 12:59
S16 0	335	semiconductor adj laser and wavelength near6 micron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20:13:07

S16 1	147	semiconductor adj laser.ti,ab,clm. and wavelength near6 micron	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 13:08
S16 2	0	semiconductor adj laser.ti,ab,clm. and wavelength near6 micron and transparent near2 resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR P	OFF	2004/06/20 13:08
S16 3	4	semiconductor adj laser.ti,ab,clm. and wavelength near6 micron and resin	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 13:20
S16 4		semiconductor adj laser.ti,ab,clm. and GaAs adj diode and resin and wavelength	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 14:21
S16 5	5334	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/06/20 14:26
S16	39	((((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50)).CCLS.) and protect\$3 and eye	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON E	2004/06/20 14:31
S16 7	5	(US-6654399-\$ or US-5745515-\$). did. or (US-20030035460-\$ or US-20030035461-\$ or US-20020154667-\$).did.	US-PGPUB; USPAT	OR	OFF	2004/06/20 14:31
S16 8	0	((US-6654399=\$ or US-5745515-\$). did. or (US-20030035460-\$ or US-20030035461-\$ or US-20020154667-\$).did.) and protect\$3 near10 eye and diffus\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ÓN	2004/06/20 14:32
S16 9	0	((US-6654399-\$ or US-5745515-\$). did. or (US-20030035460-\$ or US-20030035461-\$ or US-20020154667-\$).did.) and protect\$3 near10 eye	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/06/20 14:32
S17	597	(372/44).CCLS.	US-PGPUB;	OR	OFF	2004/06/20 14:59
0	<u></u>		USPAT; USOCR			
S17 1	999	(372/43).CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/06/20 14:59

S17 2	877	((372/43).CCLS.) not ((372/44). CCLS.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/06/20 15:00
.S17 3	11	(US-5422905-\$ or US-5488678-\$ or US-5373519-\$ or US-5105237-\$ or US-5907571-\$ or US-5734672-\$ or US-5758951-\$ or US-6654399-\$).did. or (US-20030035460-\$ or US-20030035461-\$).did.	US-PGPUB; USPAT	OR	OFF	2004/06/20 15:03
S17 4	182	((372/29.01) or (372/29.014)). CCLS.	US-PGPUB; USPAT; USOCR	OR	OFF	2004/06/20 15:08
S17 5 S17		(((372/29.01) or (372/29.014)). CCLS.) and eye (US-5383200-\$ or US-5394419-\$).	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB USPAT	OR OR	OFF	2004/06/20 15:08
6 S17 7	2	did. ((US-5383200-\$ or US-5394419-\$). did.) and eye	USPAT	OR	OFF	2004/06/20 15:12
S17 8	6	"6472705"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/08/30 14:59
S17 9	2	("6472705").PN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ΘR	OFF	2004/08/30 15:00
S18 0	5	"877844".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR ,	OFF	2004/08/30 15:00
S18 1	5904	((372/43) or (372/44) or (372/45) or (372/46) or (372/47) or (372/48) or (372/49) or (372/50) or (372/29. -01) or (372/29.014)).CCLS.	US-PGPUB; USPAT	OR	OFF	2004/12/10 08:09
S18 2	30	S181 and (protection prtoecting safety) near3 (vision eye)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 08:12

S18 3	30	S181 and (protection protecting safety) near3 (vision eye)	US-PGPUB; USPAT;	OR	OFF	2004/12/10 09:23
		, , , , , , , , , , , , , , , , , , ,	EPO; JPO; DERWENT; IBM_TDB			
S18	393	lens near3 resin and laser.ti,ab,clm.	US-PGPUB;	OR	OFF	2004/12/10 09:24
.4			USPAT; EPO; JPO; DERWENT; IBM_TDB			
S18 5	31	lens near3 resin and laser.ti,ab,clm. and (diffuse diffusion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 09:38
S18	183	(molding molded) near12 lens near12 resin and laser.ti,ab,clm.	US-PGPUB; USPAT;	OR	OFF	2004/12/10 10:04
			EPO; JPO; DERWENT; IBM_TDB			
S18 7	34	(molding molded) near12 lens near12 resin and laser.ti,ab,clm. and (safety eye diffusion diffusing scatter scattering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 09:50
S18 8	0	("encapsulat\$3near12resinnear12le nsandlaser:ti,ab,clm.	US-PGPUB; USPAT;	OR	OFF	2004/12/10 09:55
		andlightnear4(diffusionscattering)") PN:	USOCR; EPO; JPO; DERWENT; IBM_TDB			
S18 9	0	encapsulat\$3 near12 resin near12 lens and laser.ti,ab,clm. and light near4 (diffusion scattering)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 09:56
S19 0	0.	encapsulat\$3 near12 resin near12 lens and laser.ti,ab,clm. and eye near4 (safety protection protecting)	US-PGPUB; USPAT; EPO; JPO;	OR	OFF	2004/12/10 09:57
			DERWENT; IBM_TDB			
S19	0	("moldedadjlensnear12encapsulat\$ 3andlasernear3semiconductor.ti,ab,	US-PGPUB; USPAT;	OR	OFF	2004/12/10 09:57
		_clm.").PN.	EPO; JPO;- DERWENT; IBM_TDB		. : 	
S19 2	0	molded adj lens near12 encapsulat\$3 and laser near3	US-PGPUB; USPAT;	OR	OFF	2004/12/10 09:58
	r e e e	semiconductor.ti,ab,clm.	EPO; JPO; DERWENT;			
	<u> </u>		IBM_TDB			

S19 3	0	mold\$3 adj lens near12 encapsulat\$3 and laser near3 semiconductor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:58
S19 4	0	mold\$3 near12 lens near12 encapsulat\$3 and laser near3 semiconductor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	0 N	2004/12/10 09:59
S19 5	0	mold\$3 near12 lens-near12 encapsulat\$3 and laser.ti,ab,clm. and semiconductor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 09:59
S19	16	(molding molded) near12 lens near12 resin and laser.ti,ab,clm and resin near4 (mixture component multi-component)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:05
S19 7	6	(molding molded) near12 lens near12 resin and laser.ti,ab,clm. and resin near4 (mixture component multi-component) and semiconductor.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:38
S19 8		light adj diffusion near2 capability near22 resin and semiconductor near3 laser and encapsulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:39
S19 9	0	light adj diffusion near22 resin near22 encapsulat\$3 and semiconductor near3 laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:40
S20 0	Ö	resin near4 mixture and semiconductor near3 laser.ti,ab, clm. and encapsulat\$3 and lens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	⊙R	ON	2004/12/10 10:41
S20 1	0	resin near4 (multi-component mixture) and semiconductor near3 laser.ti,ab,clm. and encapsulat\$3 and lens	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:42
S20 2	82	resin near4 (multi-component mixture) and semiconductor near3 laser.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 10:42

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S20 3	17	transparent near6 resin near6 mixture and semiconductor near4 laser	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:06
S20 4	9950	((257/79) or (257/8\$1) or (257/9\$1) or (257/100) or (257/101) or (257/102) or (257/103)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 11:07
S20 5	0	S204 and mixture near25 resin near25 lens near25 encapsulat\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/12/10 11:09
S20 6	430	(372/101).CCLS.	US-PGPUB; USPAT	OR	OFF	2004/12/10 13:29
S20 7	4	"667775".AP.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 13:33
S20 8	9	encapsula\$4.clm. and resin.clm. and laser.clm. and molded.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 13:34
S20 9	1	encapsula\$4.clm. and resin.clm. and laser.clm. and molded.clm. and lens.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2004/12/10 13:34
S21 0		encapsula\$4.clm. and resin.clm. and laser.clm. and molded.clm. and lens.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM TDB	OR	ON	2004/12/10 14:15